

Abstract Submitted
for the MAR17 Meeting of
The American Physical Society

Resistive Switching and Voltage Induced Modulation of Tunneling Magnetoresistance in Nanosized Perpendicular Organic Spin Valves¹

GEORG SCHMIDT, ROBERT GOECKERITZ, NICO HOMONNAY, ALEXANDER MUELLER, Institut fuer Physik, Universitaet Halle, BODO FUHRMANN, interdisziplinaires Zentrum fuer Materialwissenschaften, Universitaet Halle — Resistive switching has already been reported in organic spin valves (OSV), however, its origin is still unclear. We have fabricated nanosized OSV based on $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3/\text{AlQ}_3/\text{Co}$. These devices show fully reversible resistive switching of up to five orders of magnitude. The magnetoresistance (MR) is modulated during the switching process from negative (-70%) to positive values (+23%). The results are reminiscent of experiments claiming magnetoelectric coupling in LSMO based tunneling structures using ferroelectric barriers. By analyzing the I/V characteristics of the devices we can show that transport is dominated by tunneling through pinholes. The resistive switching is caused by voltage induced creation and motion of oxygen vacancies at the LSMO surface, however, the resulting tunnel barrier is complemented by a second adjacent barrier in the organic semiconductor. Our model shows that the barrier in the organic material is constant, causing the initial MR while the barrier in the LMSO can be modulated by the voltage resulting in the resistive switching and the modulation of the MR as the coupling to the states in the LSMO changes. A switching caused by LSMO only is also supported by the fact that replacing ALQ_3 by H_2PC yields almost identical results.

¹Supported by the DFG in the SFB762

Georg Schmidt
Institut fuer Physik, Universitaet Halle

Date submitted: 09 Nov 2016

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